

1. Description

The UMW IRS2304STR is a high voltage, high speed power MOSFET drivers with dependent high and low-side referenced output channels. Proprietary HVIC and latch immune CMOS technologies enable ruggedized monolithic construction. The logic input is compatible with standard CMOS or LSTTL output, down to 3.3V logic. The output drivers feature a high pulse current buffer stage designed for minimum driver cross-conduction. The UMW IRS2304STR is integrated with a bootstrap diode to charge the high side, simplifying the peripheral circuit of the chip. The floating channel can be used to drive an N-channel power MOSFET in the high-side configuration which operates up to 700V.

3. Features

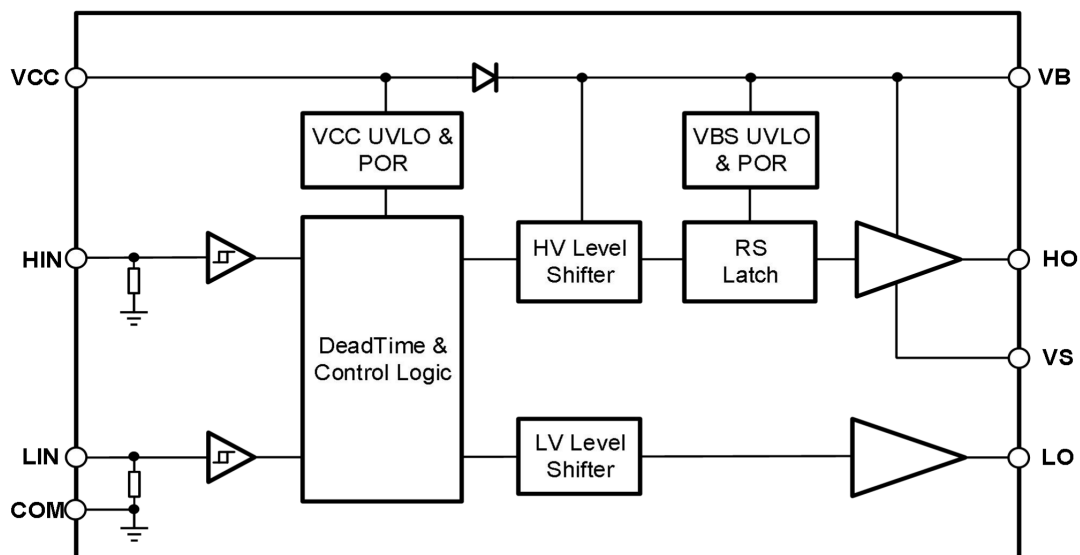
- Floating channel designed for bootstrap operation
- Fully operational to +700 V
- 3.3V, 5V and 15V input logic compatible
- Tolerant to negative transient voltage,
- dV/dt immune
- Allowable negative Vs capability: -9V
- Gate drive supply range from 10V to 20V

2. Applications

- Motor Control
- Air Conditioners/ Washing Machines
- General Purpose Inverters
- Micro/Mini Inverter Drives
- Matched propagation delay for both channels
- Wide operating temperature range
-40°C ~125°C
- Cross-conduction prevention
- Internal 100ns deadtime
- Typically output Source/Sink current capability: 300mA/600mA

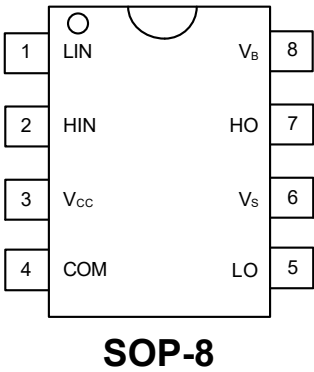


4.Functional Block Diagram





5.Pinning Information



Lead Definitions

Number	Symbol	Description
1	LIN	Logic input for low side gate driver output (LO), in phase
2	HIN	Logic input for high side gate driver output (HO), in phase
3	V _{CC}	Low side and logic fixed supply
4	COM	Low side return
5	LO	Low side gate drive output
6	V _S	High side floating supply return
7	HO	High side gate drive output
8	V _B	High side floating supply



6. Absolute Maximum Ratings

Exceeding the limit maximum rating may cause permanent damage to the device. All voltage parameters are rated with reference to V_{SS} and an ambient temperature of 25°C.

Parameter	Symbol	Min	Max	Units
High side floating supply	V_B	-0.3	725	V
High side floating supply return	V_S	V_B-25	$V_B+0.3$	V
High side gate drive output	V_{HO}	$V_S-0.3$	$V_B+0.3$	V
Low side and main power supply	V_{CC}	-0.3	25	V
Low side gate drive output	V_{LO}	-0.3	$V_{CC}+0.3$	V
Logic input of HIN & LIN	V_{IN}	-0.3	$V_{CC}+0.3$	V
Allowable Offset Supply Voltage Transient	dV_S/dt		50	V/ns
HBM Model	ESD	1500		V
Machine Model		500		V
Package Power Dissipation @ $T_A \leq 25^\circ\text{C}$	P_D		625	mW
Thermal Resistance, Junction to Ambient	R_{thJA}		200	$^\circ\text{C/W}$
Junction Temperature	T_J		150	$^\circ\text{C/W}$
Storage Temperature	T_S	-55	150	$^\circ\text{C}$
Lead Temperature (Soldering, 10 seconds)	T_L		300	$^\circ\text{C/W}$



7. Recommended Operating Conditions

For proper operation, the device should be used under the following recommended conditions. The bias ratings of V_S and V_{SS} are measured at a supply voltage of 15V, and unless otherwise specified, the ratings of all voltage parameters are referenced to V_{SS} and the ambient temperature is 25°C.

Parameter	Symbol	Min	Max	Units
High side floating supply	V_B	$V_S + 10$	$V_S + 20$	V
High side floating supply return	V_S	-9	700	V
High side gate drive output	V_{HO}	V_S	V_B	V
Low side and main power supply	V_{CC}	10	20	V
Low side gate drive output	V_{LO}	0	V_{CC}	V
Logic input of HIN & $\overline{LIN}$	V_{IN}	0	V_{CC}	V
Ambient temperature	T_A	-40	125	°C

Note1: Transient negative V_S can be used for COM-50V with a pulse width of 50ns, guaranteed by design.

Note2: When the input pulse width is less than 1us, the input pulse cannot be transmitted normally.

8. Electrical Characteristics

Valid for temperature range at $T_A=25^\circ\text{C}$, $V_{CC}=V_B=15\text{V}$, $C_L=1\text{nF}$, unless otherwise specified.

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Turn-on propagation delay	t_{ON}	$V_S=0\text{V}$		130	200	ns
Turn-off propagation delay	t_{OFF}	$V_S=700\text{V}$		130	200	ns
Turn-on rise time	t_R			75	130	ns
Turn-off fall time	t_F			35	70	ns
Deadtime	DT		80	100	190	ns
Matched propagation time delay	MT				50	ns
Matched deadtime delay	MDT				60	ns



9.Static Electrical Characteristics

Valid for temperature range at $T_A=25^{\circ}\text{C}$, $V_{CC}=V_B=15\text{V}$, $C_L=1\text{nF}$, unless otherwise specified.

Parameter	Symbol	Conditions	Min	Typ	Max	Units
V_{CC} and V_{BS} supply UVLO threshold	V_{CCUV+}		8	8.9	9.8	V
	V_{BSUV+}					
	V_{CCUV-}		7.4	8.2	9	V
	V_{BSUV-}					
hysteresis of V_{CC} and V_{BS} UVLO	$V_{CCUVHYS}$			0.7		V
	$V_{BSUVHYS}$					
High-side floating supply leakage current	I_{LK}	$V_B=V_S=700\text{V}$			50	μA
Quiescent V_B supply current	I_{QBS}	$V_{IN}=0\text{V}$ or 5V		50	100	μA
Quiescent V_{CC} supply current	I_{QCC}	$V_{IN}=0\text{V}$ or 5V		120	240	μA
Logic "1"(HIN&LIN) input voltage	V_{IH}	$V_{CC}=10\text{V}$ to 20V	2.5			V
Logic "0"(HIN&LIN) input voltage	V_{IL}	$V_{CC}=10\text{V}$ to 20V			0.8	V
High level output voltage, $V_{BIAS}-V_O$	V_{OH}	$I_O=0\text{A}$			0.1	V
Low level output voltage, V_O	V_{OL}	$I_O=0\text{A}$			0.1	V
Logic "1"input bias current	I_{IN+}	$I_N=5\text{V}$		5	10	μA
Logic "0" input bias current	I_{IN-}	$I_N=0\text{V}$			2	μA
Output high short circuit pulsed current	I_{O+}	$V_O=0\text{V}$, $PW\leq 10\mu\text{s}$	200	300		mA
Output low short circuit pulsed current	I_{O-}	$V_O=15\text{V}$, $PW\leq 10\mu\text{s}$	400	600		mA
Bootstrap diode conduction voltage	V_{BSD}	$I_{BSD}=1\text{mA}$		0.6		V
Bootstrap diode conduction resistance	R_{BSD}	$I_{BSD}=10\text{mA}$		200		Ω



10.Function Description

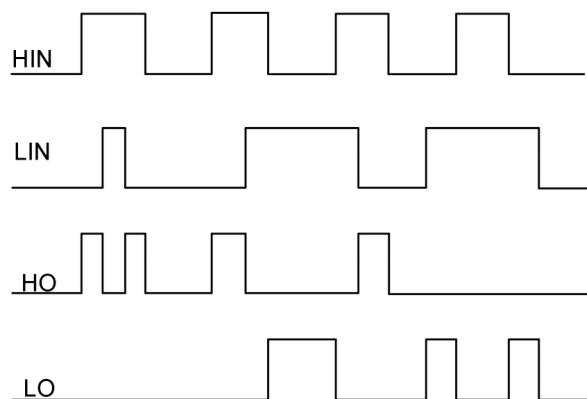


Figure 1. UMW IRS2304STR Input and output timing waveform

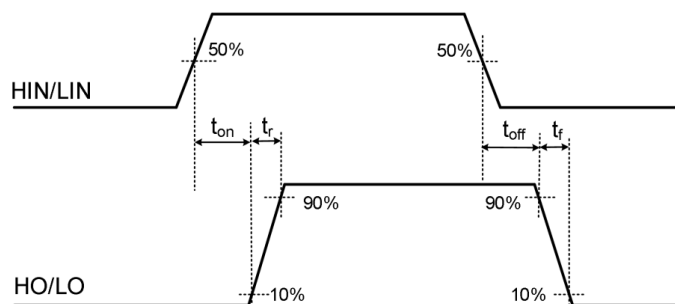


Figure 2. Propagation Time Waveform Definition

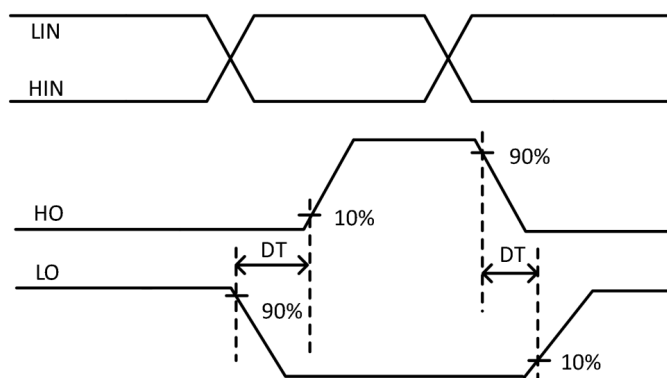


Figure 3. Cross Conduction Prevention Delay Time Waveform Definition



11.Function Block Diagram

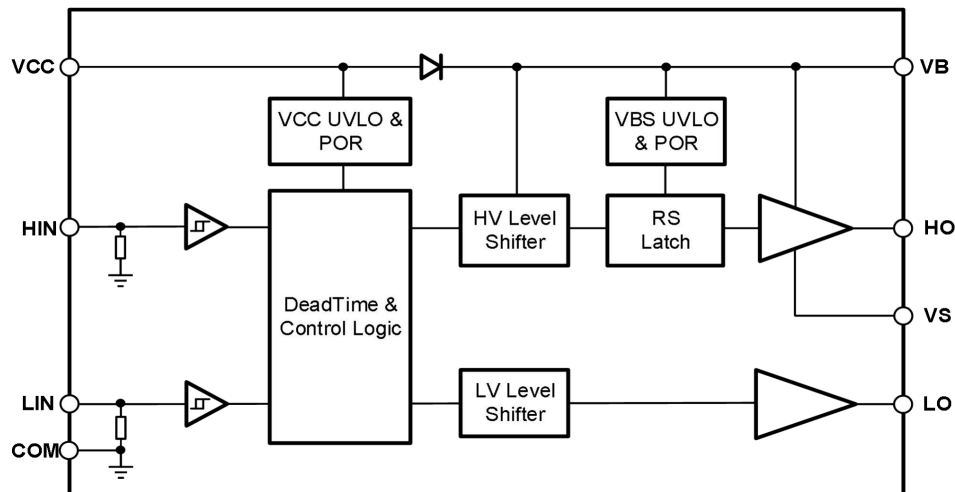


Figure 4. Function Block Diagram of UMW IRS2304STR

12.Application Message

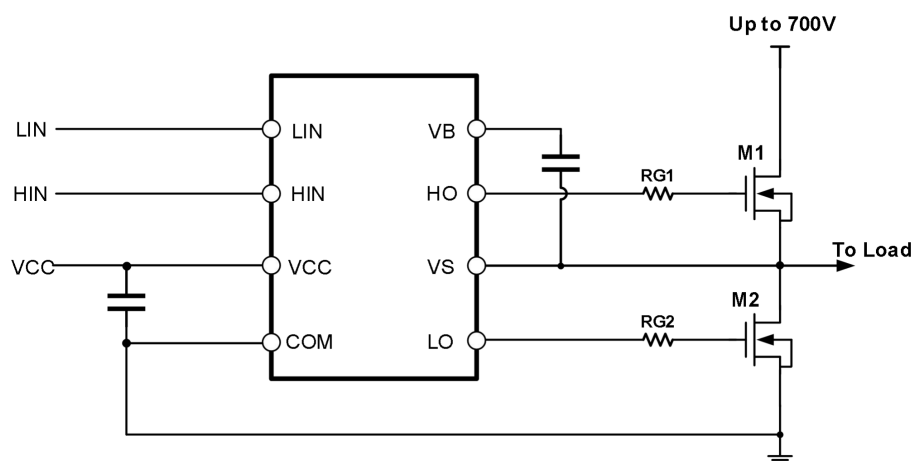
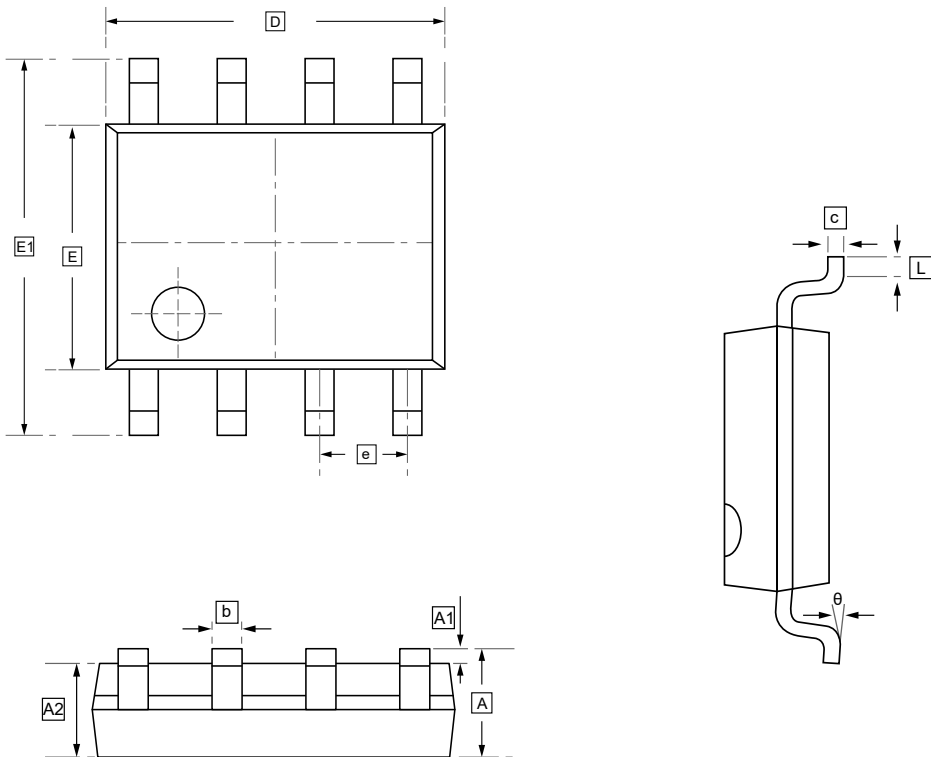


Figure 5. Typical application circuit of UMW IRS2304STR



13.SOP-8 Package Outline Dimensions

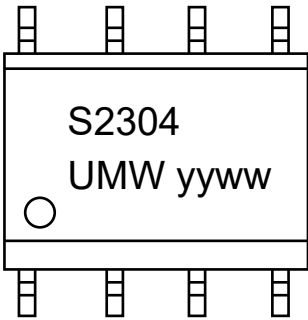


DIMENSIONS (mm are the original dimensions)

Symbol	A	A1	A2	b	c	D	E	E1	e	L	θ
Min	1.350	0.000	1.350	0.330	0.170	4.700	3.800	5.800	1.270	0.400	0°
Max	1.750	0.100	1.550	0.510	0.250	5.100	4.000	6.200	BSC	1.270	8°



14.Ordering information



yy: Year Code
ww: Week Code

Order Code	Package	Base QTY	Delivery Mode
UMW IRS2304STR	SOP-8	2500	Tape and reel



15.Disclaimer

UMW reserves the right to make changes to all products, specifications. Customers should obtain the latest version of product documentation and verify the completeness and currency of the information before placing an order.

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